

	Hits	Search Text	DBs
1	2	micromachin\$4 and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch\$4 or RIE) same undercut\$4) and (etch\$4 same isotropic\$6) and (passivat\$9 same conformal\$6) and ((etch\$4 same passivat\$6) same 9alternat\$4 or subsequent\$4 or simultaneous\$5)) and (etch\$4 near16 (time or second or minute)) and (passivat\$4 same (time or second or minute)) and undercut\$4 and (alter\$4 same (passivat\$4 or etch\$4 same undercut\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	2	micromachin\$4 and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch\$4 or RIE) same undercut\$4) and (etch\$4 same isotropic\$6) and (passivat\$9 same conformal\$6) and ((etch\$4 same passivat\$6) same (alternat\$4 or subsequent\$4 or simultaneous\$5)) and (etch\$4 near16 (time or second or minute)) and (passivat\$4 same (time or second or minute)) and undercut\$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
3	24	(("5198390") or ("5199917") or ("5235187") or ("5287082") or ("5316979") or ("5363021") or ("5375033") or ("5393375") or ("5399415") or ("5436070") or ("5449903") or ("5506175") or ("5546988") or ("5563343") or ("5610335") or ("5627427") or ("5628917") or ("5637539") or ("5640133") or ("5846849") or ("5847454") or ("5501893") or ("5498312") or ("5856722"))).PN.	US-PGPUB; USPAT
4	2	micromachin\$4 and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch\$4 or RIE) same undercut\$4) and (etch\$4 same isotropic\$6) and passivat\$9 and conformal\$6 and (((etch\$4 or RIE) same passivat\$6) same (alternat\$4 or subsequent\$4 or simultaneous\$5)) and (etch\$4 near16 (rate or time or second or minute)) and (passivat\$4 same (rate or time or second or minute)) and undercut\$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	2	micromachin\$4 and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch\$4 or RIE) same undercut\$4) and (etch\$4 same isotropic\$6) and (SiO\$2 or passivat\$9 or (thermal\$3 near9 oxid\$5)) and conformal\$6 and (((etch\$4 or RIE) same (oxidi\$6 or passivat\$6)) same (alternat\$4 or subsequent\$4 or simultaneous\$5)) and (etch\$4 near16 (rate or time or second or minute)) and ((SiO\$3 or (thermal\$4 near9 oxid\$6) or passivat\$4) same (rate or time or second or minute)) and undercut\$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	2	micromachin\$4 and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch\$4 or RIE) same undercut\$4) and (etch\$4 same isotropic\$6) and (SiO\$2 or passivat\$9 or (thermal\$3 near9 oxid\$5)) and (((etch\$4 or RIE) same (oxidi\$6 or passivat\$6)) same (alternat\$4 or subsequent\$4 or simultaneous\$5)) and (etch\$4 near16 (rate or time or second or minute)) and ((SiO\$3 or (thermal\$4 near9 oxid\$6) or passivat\$4) same (rate or time or second or minute)) and undercut\$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	2	(micromachin\$4 or (micro near4 mechan\$5)) and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch\$4 or RIE) same undercut\$4) and (etch\$4 same isotropic\$6) and (SiO\$2 or passivat\$9 or (thermal\$3 near9 oxid\$5)) and (((etch\$4 or RIE) same (oxidi\$6 or passivat\$6)) same (alternat\$4 or subsequent\$4 or simultaneous\$5)) and (etch\$4 near16 (rate or time or second or minute)) and ((SiO\$3 or (thermal\$4 near9 oxid\$6) or passivat\$4) same (rate or time or second or minute)) and undercut\$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	45	(micromachin\$4 or (micro near4 mechan\$5)) and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch\$4 or RIE)) and (etch\$4 same isotropic\$6) and (SiO\$2 or passivat\$9 or (thermal\$3 near9 oxid\$5)) and (((etch\$4 or RIE) same (oxidi\$6 or passivat\$6)) same (alternat\$4 or subsequent\$4 or simultaneous\$5)) and (etch\$4 near16 (rate or time or second or minute)) and ((SiO\$3 or (thermal\$4 near9 oxid\$6) or passivat\$4) same (rate or time or second or minute)) and undercut\$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	0	(micromachin\$4 or (micro near8 mechan\$5) or MEMS) and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch\$4 or RIE)) and (etch\$4 same isotropic\$6) and (SiO\$2 or passivat\$9 or (thermal\$3 near9 oxid\$5)) and (((etch\$4 or RIE) same (oxidi\$6 or passivat\$6)) same (alternat\$4 or subsequent\$4 or simultaneous\$5)) and ((SiO\$3 or (thermal\$4 near9 oxid\$6) or passivat\$4) same (rate or time or second or minute)) and undercut\$4 and ((first near14 release near9 structure) same (underly\$4 or (self\$4align\$4) or beneath or bottom) same (second near12 release near9 structure) same (different or vary\$4 or non\$4uniform) same (topograph\$4 or width or breadth or diameter or dimension\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB